

ABSTRACT OF THE DISCLOSURE

A III group nitride system compound semiconductor light emitting element has a quantum well structure that includes a well layer of $\text{Al}_{x_1}\text{Ga}_{y_1}\text{In}_{1-x_1-y_1}\text{N}$, where $0 < x_1$, $0 \leq y_1$ and $x_1 + y_1 < 1$ and
5 a barrier layer of $\text{Al}_{x_2}\text{Ga}_{y_2}\text{In}_{1-x_2-y_2}\text{N}$, where $0 < x_2$, $0 \leq y_2$ and $x_2 + y_2 < 1$. The Al composition (x_2) of barrier layer is equal to or smaller than that (x_1) of well layer.